



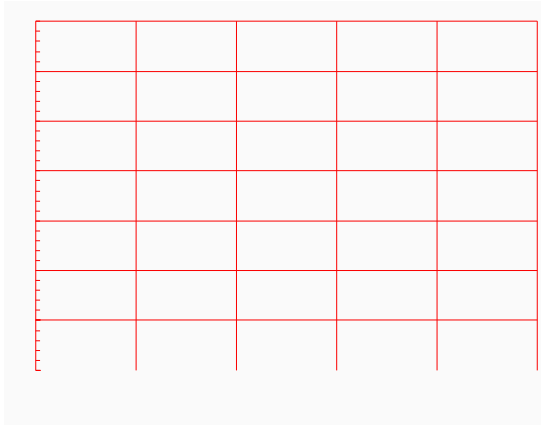
Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	10	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	0.5	kV

( $T_j=25$  unless otherwise specified)

<b>Symbol</b>	<b>Test Condition</b>	<b>Value</b>	<b>Unit</b>
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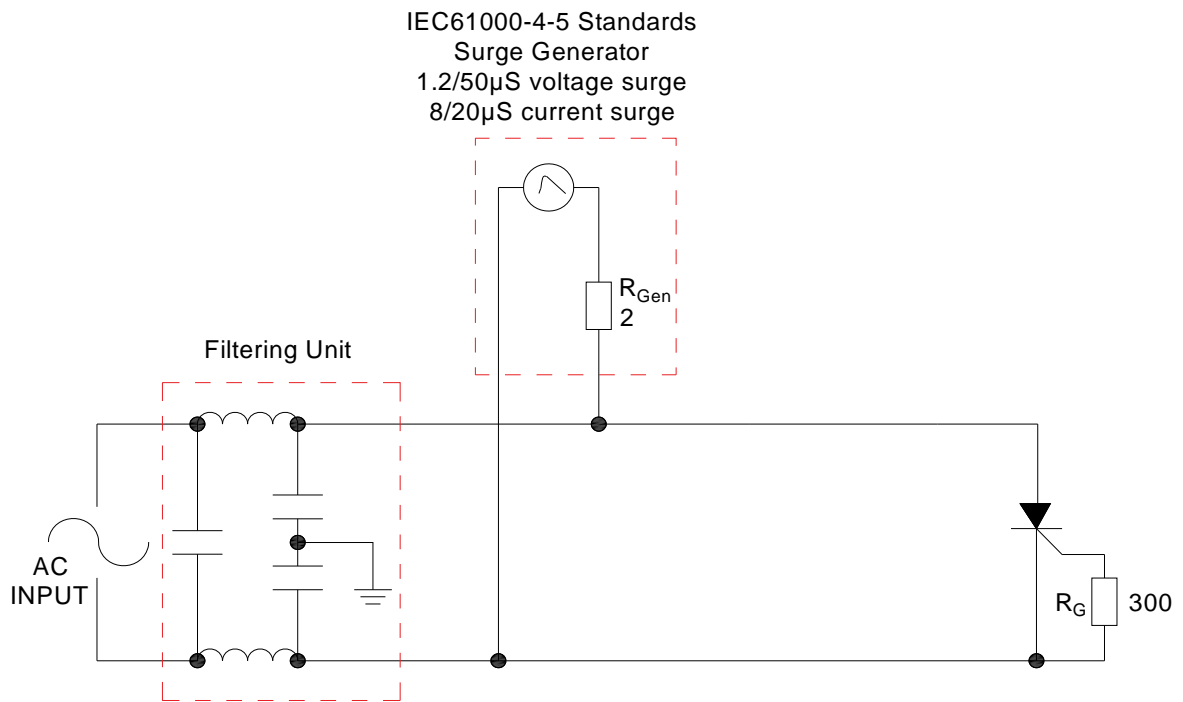


**FIG.1:** Maximum power dissipation versus RMS on-state current



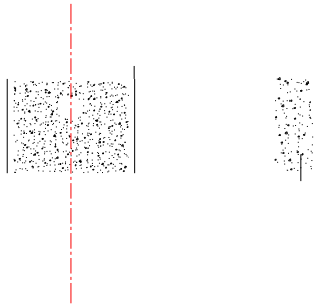
**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.




Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie





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